

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^d	Q _g (Typ.)
- 20	0.0062 at V _{GS} = - 4.5 V	- 26.6	59 nC
	0.0105 at V _{GS} = - 2.5 V	- 20.6	

FEATURES

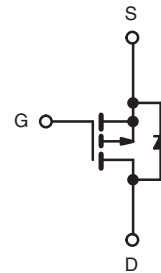
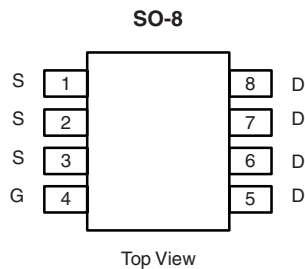
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch
- Adapter Switch
 - Notebook
 - Game Station



Ordering Information: Si4477DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 20	V	
Gate-Source Voltage	V _{GS}	± 12		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 26.6	A
		T _C = 70 °C	- 21.3	
		T _A = 25 °C	- 18 ^{a, b}	
		T _A = 70 °C	- 14.5 ^{a, b}	
Pulsed Drain Current	I _{DM}	- 60		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	- 5.5	
		T _A = 25 °C	- 2.5 ^{a, b}	
Avalanche Current	I _{AS}	30		
Single-Pulse Avalanche Energy	E _{AS}	45	mJ	
Maximum Power Dissipation	P _D	T _C = 25 °C	6.6	W
		T _C = 70 °C	4.2	
		T _A = 25 °C	3 ^{a, b}	
		T _A = 70 °C	1.95 ^{a, b}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R _{thJA}	34	41	°C/W
Maximum Junction-to-Foot	R _{thJF}	15	19	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 80 °C/W.
- Based on T_C = 25 °C.

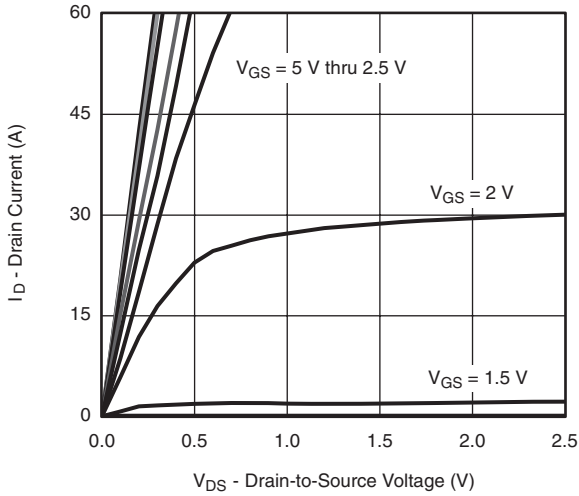
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-13		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		4.1			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.6		-1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}, V_{GS} = -4.5\text{ V}$	-30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -18\text{ A}$		0.0051	0.0062	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -14\text{ A}$		0.0085	0.0105	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -3.5\text{ A}$		10		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		4600		pF
Output Capacitance	C_{oss}		980			
Reverse Transfer Capacitance	C_{rss}		175			
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -10\text{ V}, I_D = -18\text{ A}$		125	190	nC
			59	90		
Gate-Source Charge	Q_{gs}	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -18\text{ A}$		10		nC
Gate-Drain Charge	Q_{gd}		19			
Gate Resistance	R_g		$f = 1\text{ MHz}$		1.3	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		13	20	ns
Rise Time	t_r		10	20		
Turn-Off Delay Time	$t_{d(off)}$		100	150		
Fall Time	t_f		25	40		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		42	60	ns
Rise Time	t_r		42	60		
Turn-Off Delay Time	$t_{d(off)}$		100	150		
Fall Time	t_f		42	60		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-5.5	A
Pulse Diode Forward Current	I_{SM}				-60	
Body Diode Voltage	V_{SD}	$I_S = -5\text{ A}, V_{GS} = 0\text{ V}$		-0.75	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		42	60	ns
Body Diode Reverse Recovery Charge	Q_{rr}		40	60	nC	
Reverse Recovery Fall Time	t_a		20		ns	
Reverse Recovery Rise Time	t_b		22			

Notes:

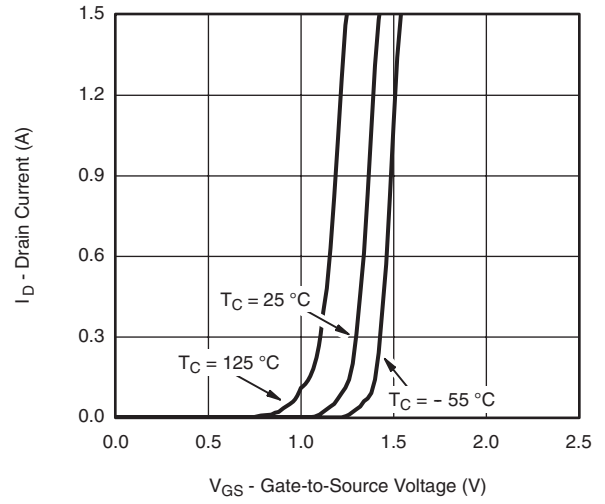
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

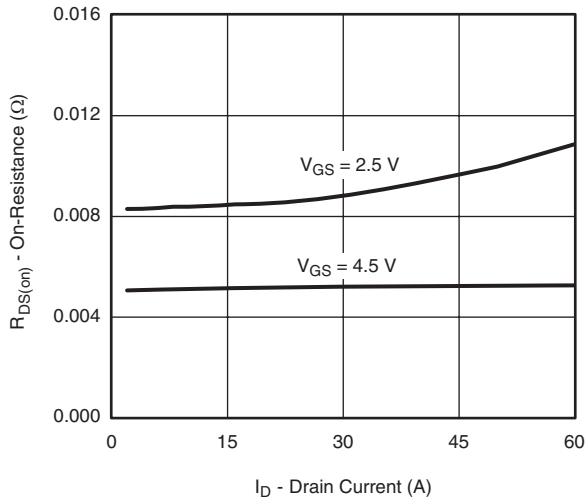
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



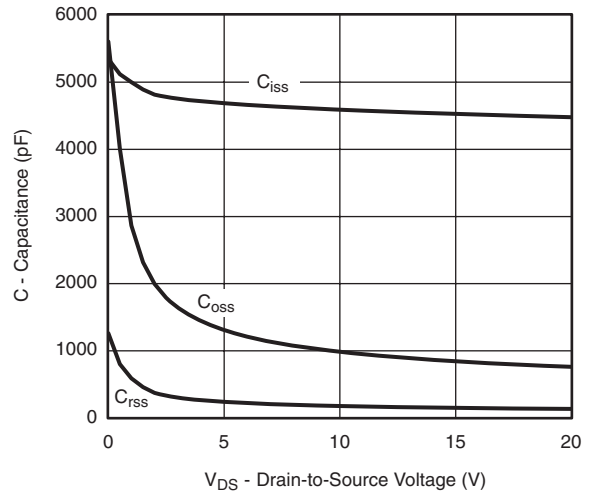
Output Characteristics



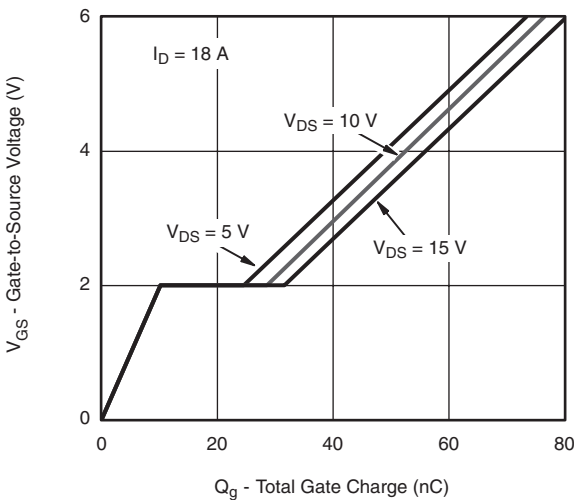
Transfer Characteristics



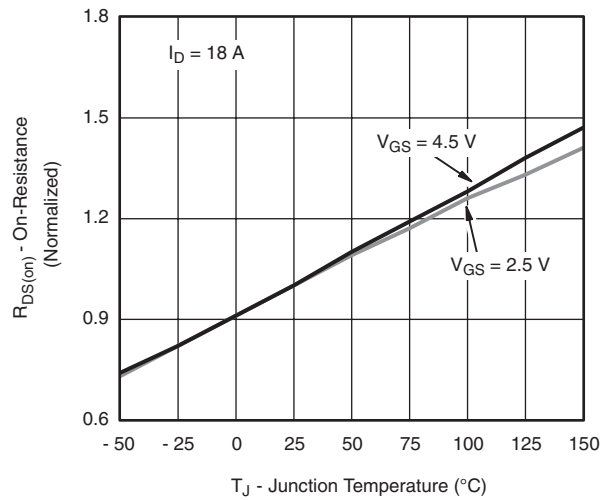
On-Resistance vs. Drain Current



Capacitance

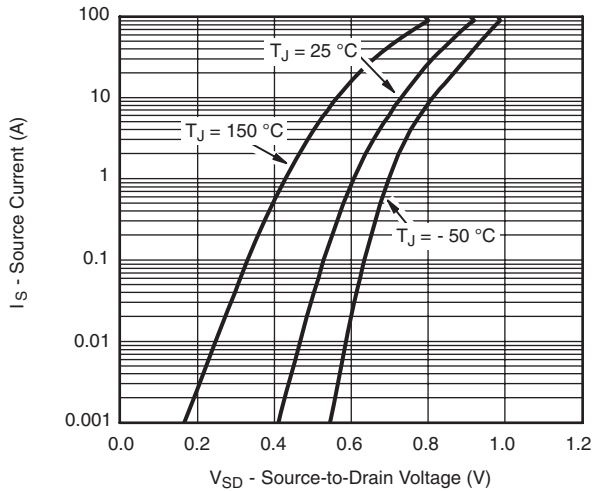


Gate Charge

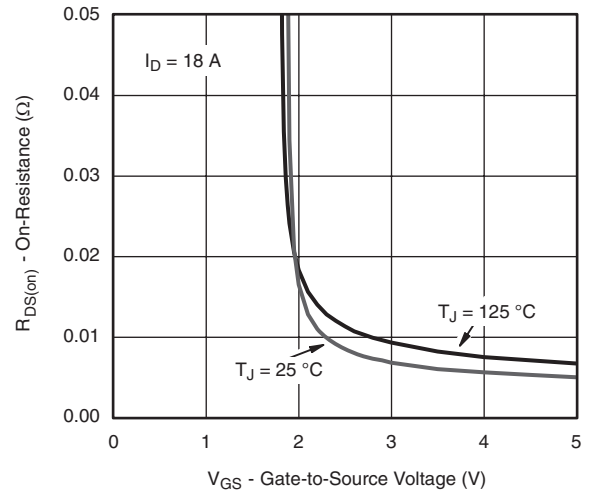


On-Resistance vs. Junction Temperature

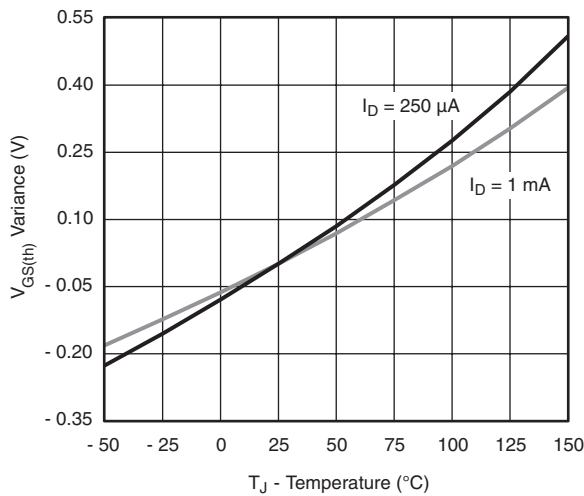
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



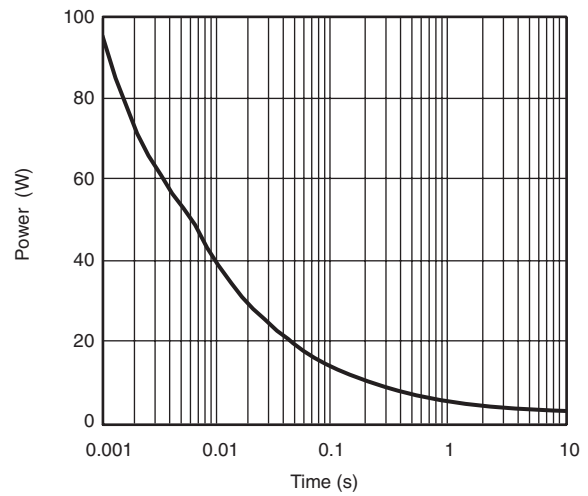
Source-Drain Diode Forward Voltage



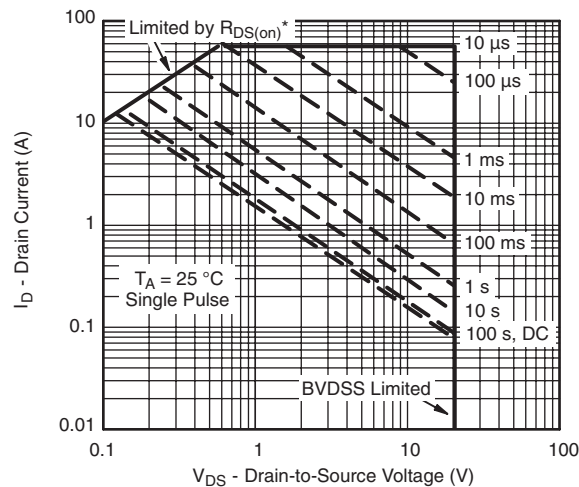
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



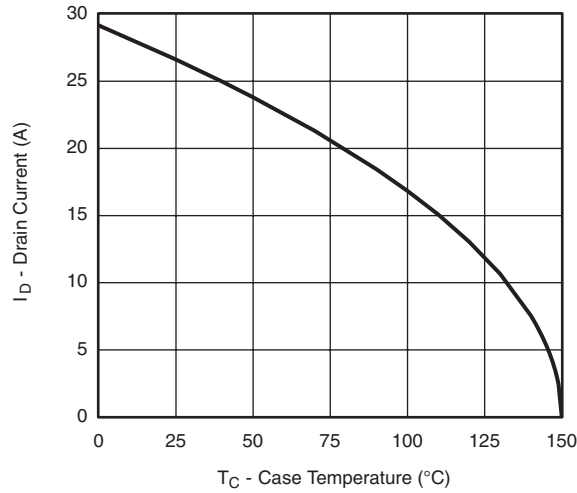
Single Pulse Power, Junction-to-Ambient



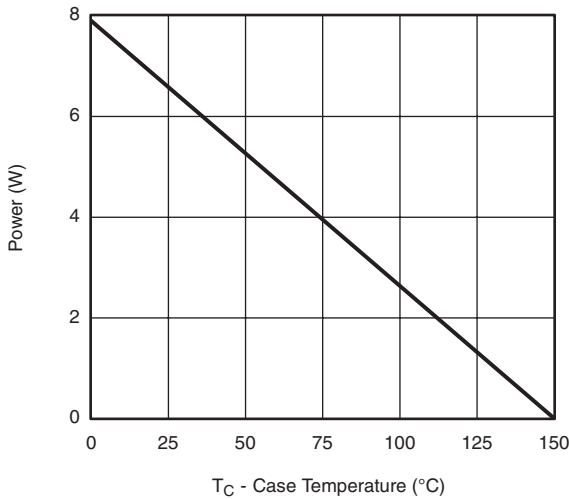
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

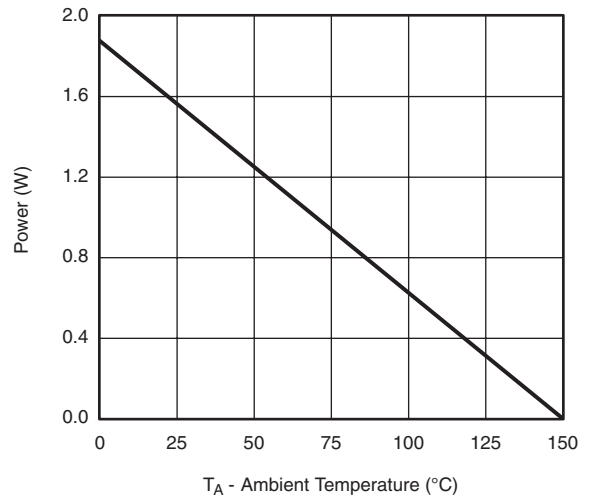
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



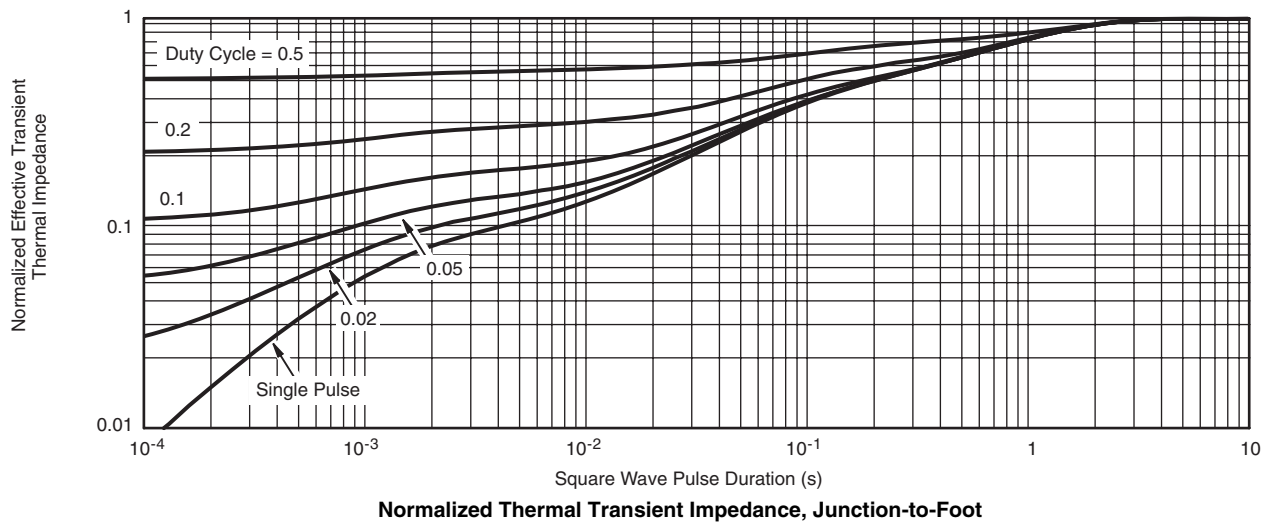
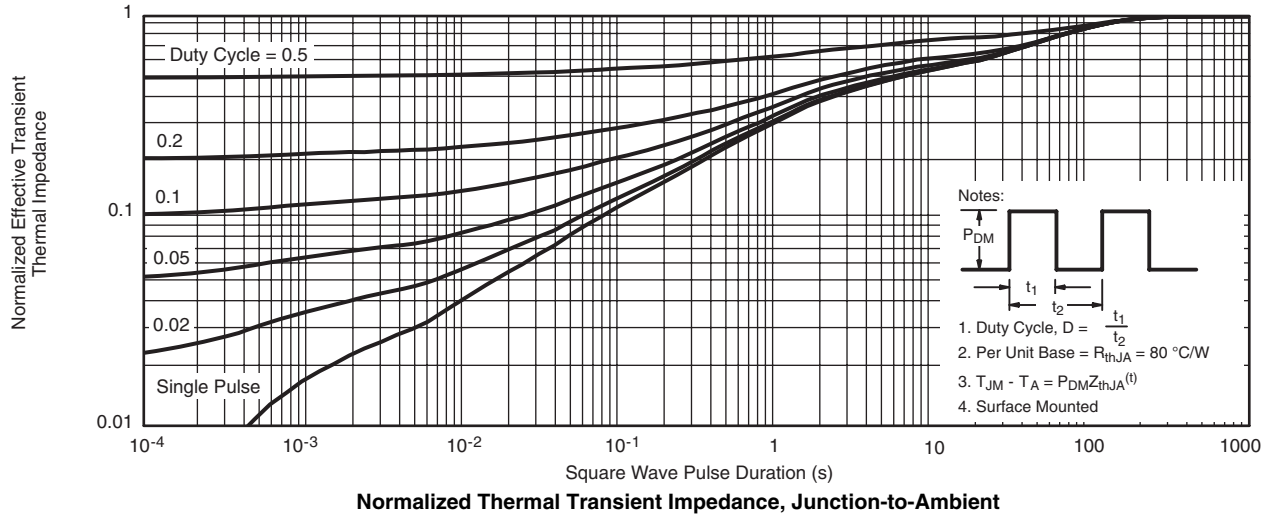
Power, Junction-to-Foot



Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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